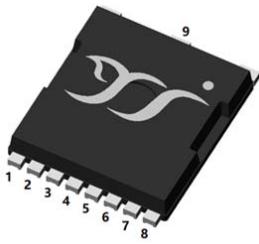
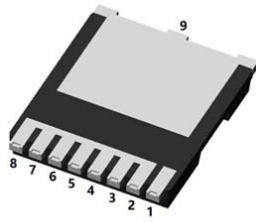


N-Channel Enhancement Mode Field Effect Transistor

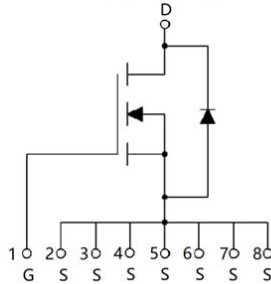


Top View



Bottom View

TOLL



Product Summary

- V_{DS} 40V
- I_D 225A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $< 1.2m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- High power inverter system
- Uninterruptible power supply
- LCDM appliances

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	25	A
	$T_A=100^\circ C$		17.8	
	$T_C=25^\circ C$		225	
	$T_C=100^\circ C$		159	
Pulsed Drain Current ^A		I_{DM}	400	A
Avalanche energy ^B		EAS	1441	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	2	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		166	
	$T_C=100^\circ C$		83	
Junction and Storage Temperature Range		T_J, T_{STG}	$-55 \sim +175$	$^\circ C$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	60	72	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.75	0.9	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJT225G04HJQ	F1	YJT225G04HJ	2000	4000	20000	13" reel



YJT225G04HJQ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =1mA	2	2.5	3	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =75A	-	0.9	1.2	mΩ
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.75	1.2	V
Gate resistance	R _G	f=1MHz	-	3	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	225	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	6830	-	pF
Output Capacitance	C _{oss}		-	1970	-	
Reverse Transfer Capacitance	C _{rss}		-	148	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =20V, I _D =50A	-	84.3	-	nC
Gate-Source Charge	Q _{gs}		-	30	-	
Gate-Drain Charge	Q _{gd}		-	11.46	-	
Reverse Recovery Charge	Q _{rr}	I _F =50A, di/dt=100A/us	-	63	-	nC
Reverse Recovery Time	t _{rr}		-	58	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =20V, I _D =50A R _{GEN} =2.5Ω	-	18	-	ns
Turn-on Rise Time	t _r		-	13	-	
Turn-off Delay Time	t _{D(off)}		-	58	-	
Turn-off fall Time	t _f		-	28	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=100V, V_G=10V, L=3mH, I_{AS}=31A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.



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Typical Electrical and Thermal Characteristics Diagrams

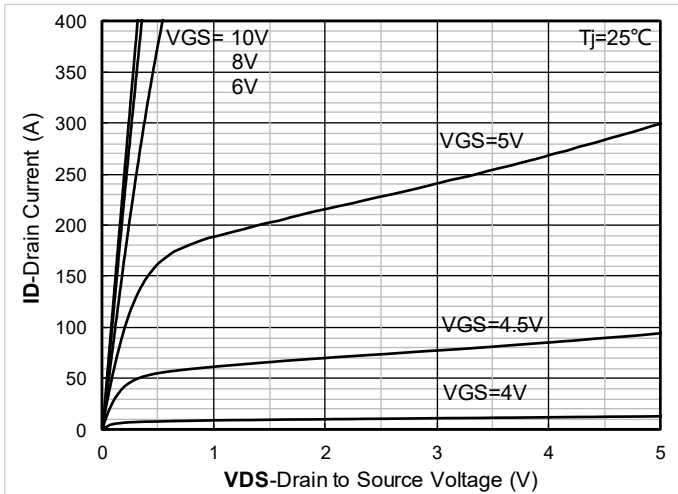


Figure 1. Output Characteristics

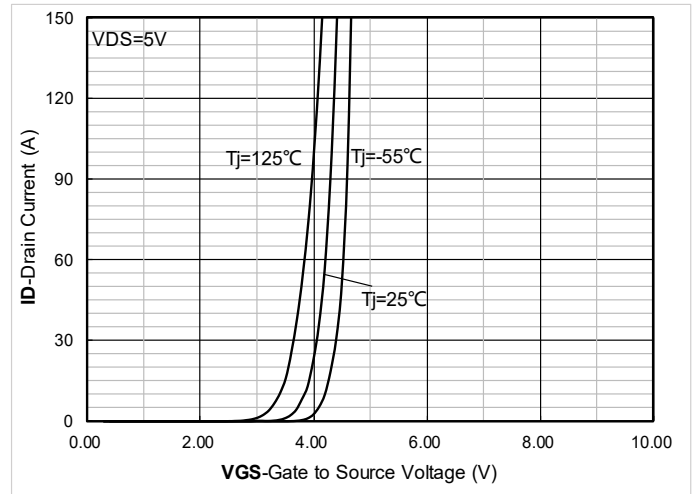


Figure 2. Transfer Characteristics

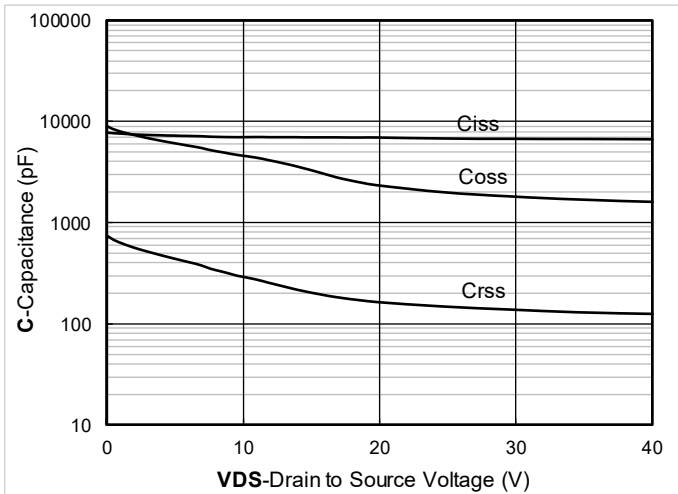


Figure 3. Capacitance Characteristics

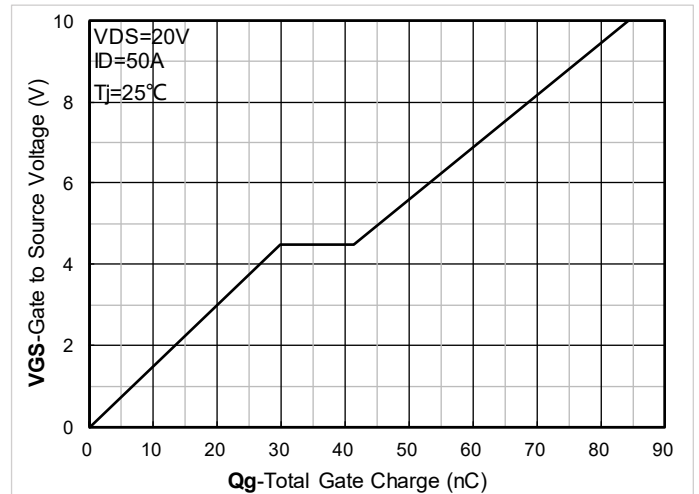


Figure 4. Gate Charge

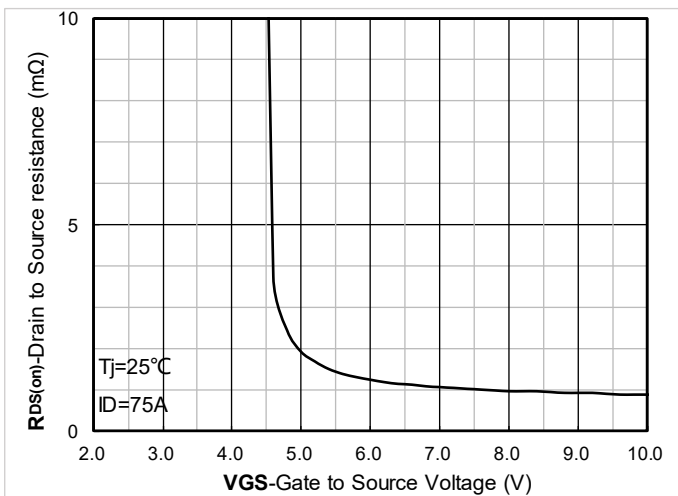


Figure 5. On-Resistance vs Gate to Source Voltage

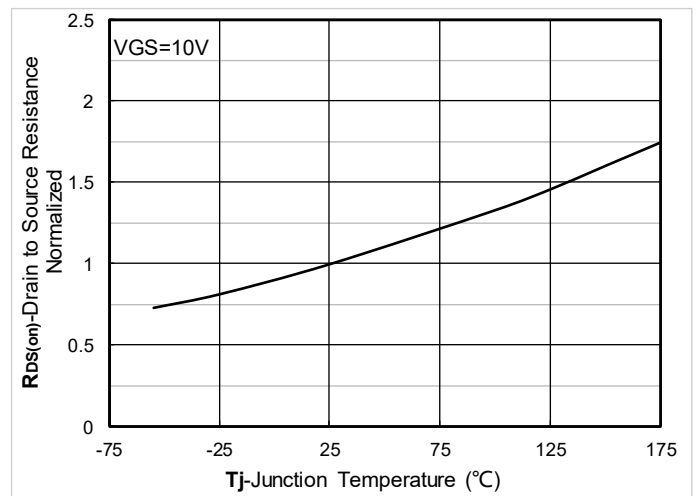


Figure 6. Normalized On-Resistance



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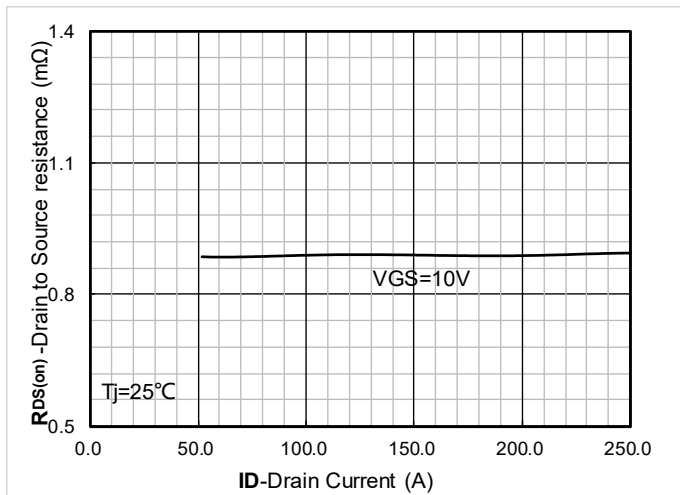


Figure 7. $R_{DS(on)}$ VS Drain Current

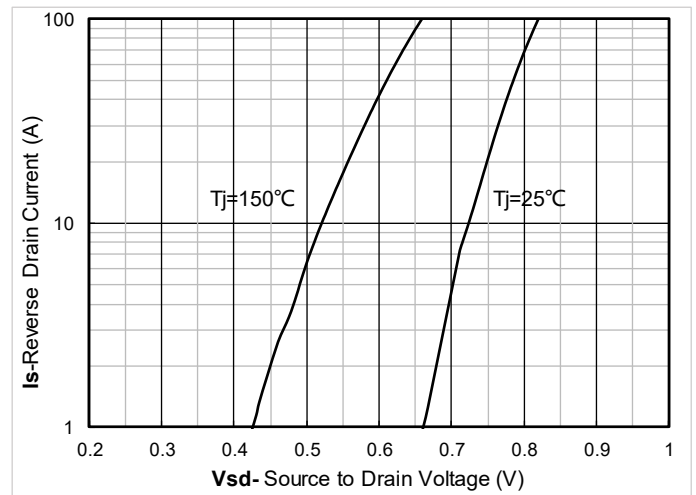


Figure 8. Forward characteristics of reverse diode

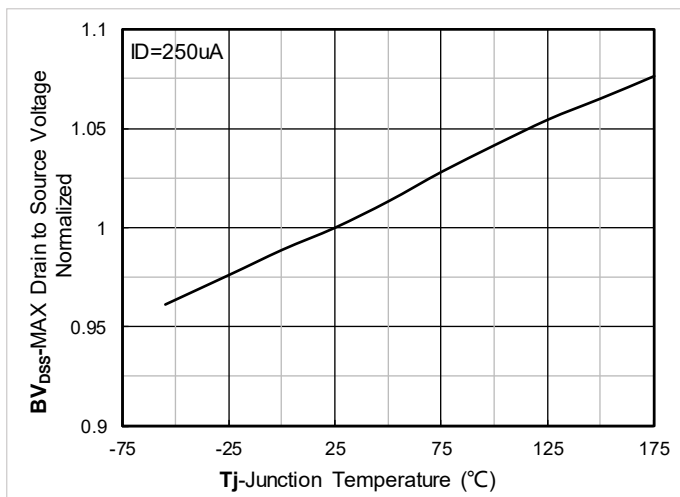


Figure 9. Normalized breakdown voltage

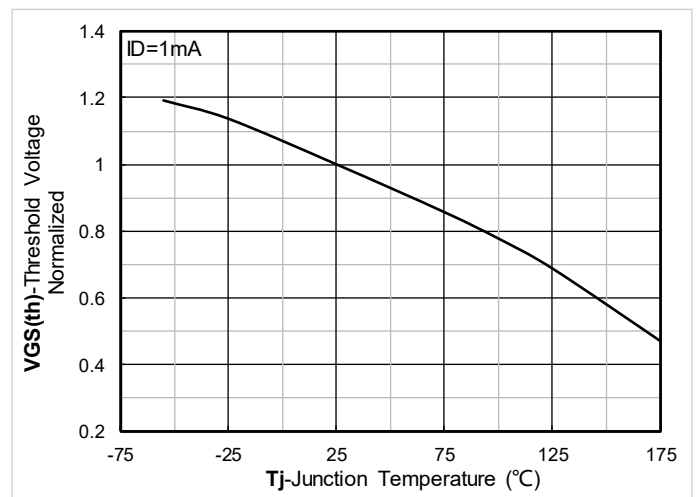


Figure 10. Normalized Threshold voltage

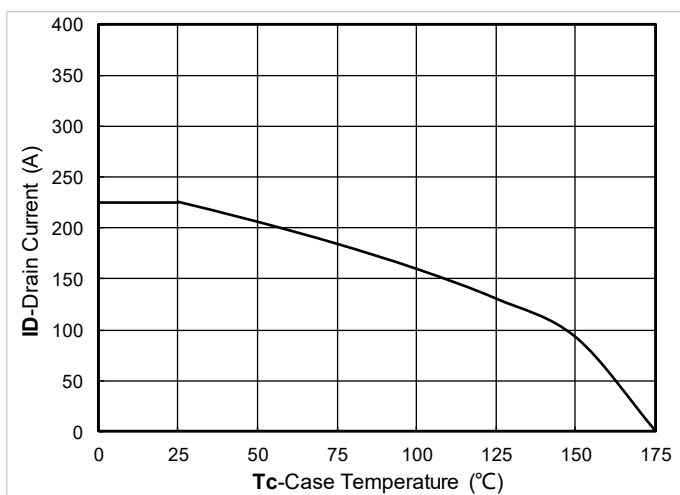


Figure 11. Current dissipation

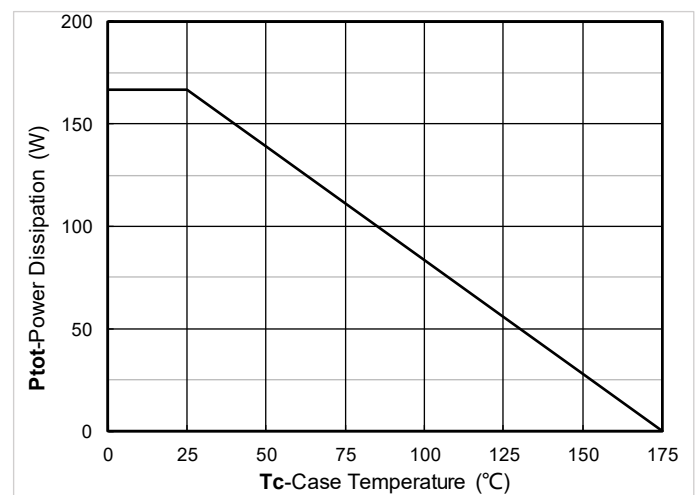


Figure 12. Power dissipation



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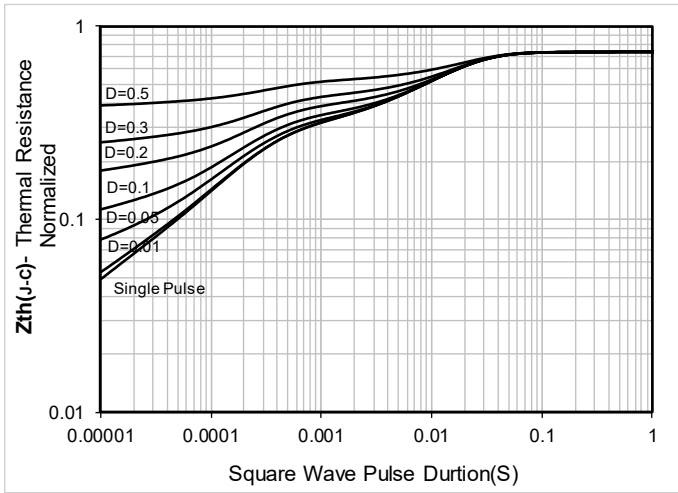


Figure 13. Maximum Transient Thermal Impedance

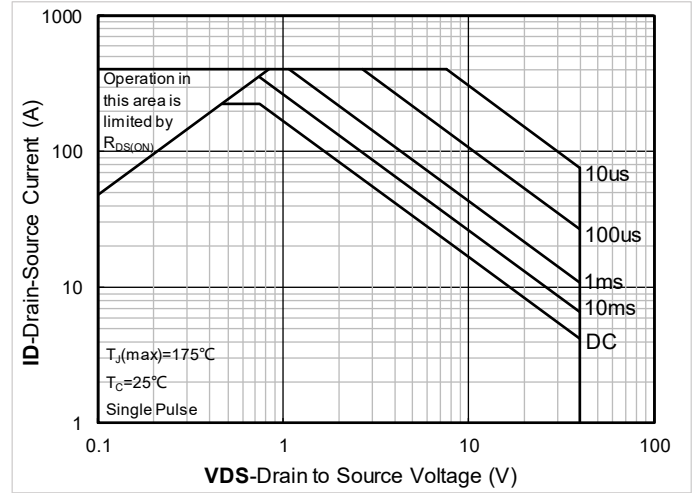
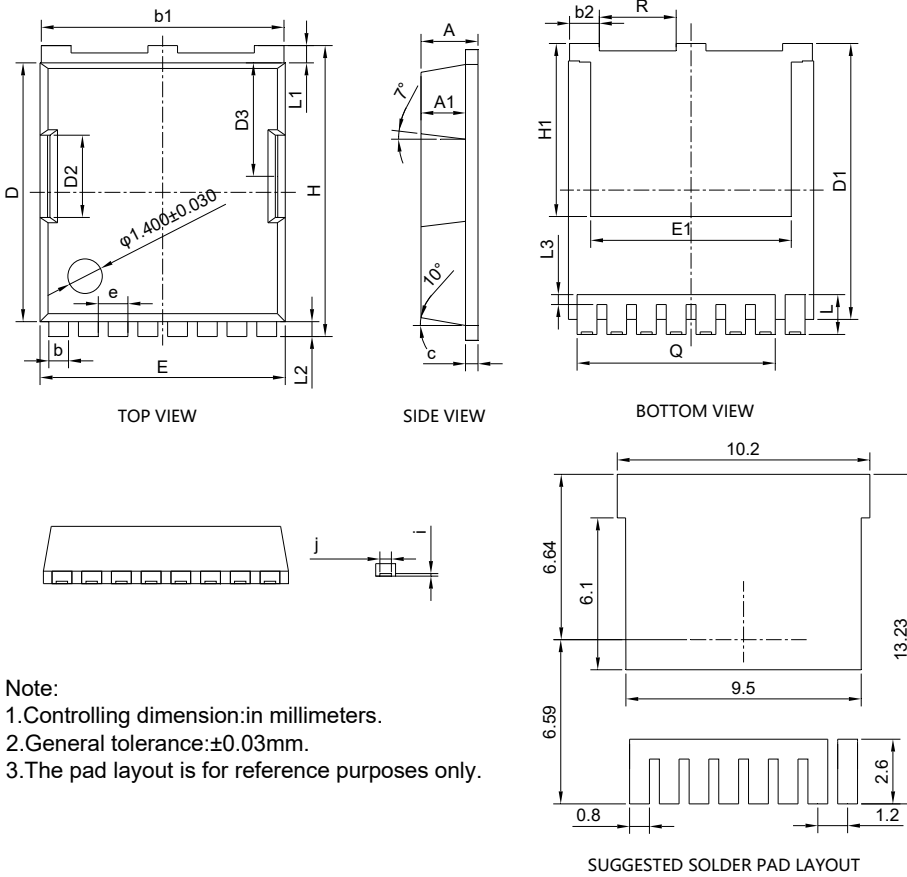


Figure 14. Safe Operation Area



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■ TOLL Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4	0.5	0.6
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.2	3.3	3.4
D3	4.45	4.55	4.65
E	9.8	9.9	10
E1	8	8.1	8.2
e	1.2 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
i	0.1 REF		
j	0.46 REF		
L	1.5	1.6	1.7
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L3	0.3	0.4	0.5
Q	8 REF		
R	3.0	3.1	3.2

Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.03 mm.
 3. The pad layout is for reference purposes only.

UNIT: mm



YJT225G04HJQ

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